S12	1811	cmos near2 sensor and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/31 08:47
S11	7	coms near2 sensor and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/31 08:47
S14	1032	single adj1 crystal and image adj1 sensor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 15:20
S1	5	(("6429036") or ("6501065") or ("6344368") or ("6344669") or ("20030025160")).PN.	US-PGPUB; USPAT	OR	OFF	2006/02/06 15:20
S15	496	S14 and gate adj1 electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 15:21
S16	421	S15 and "257"/$$$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 15:55
S17	222	S15 and "438"/$$$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 16:39
L1	31754	single adj1 crystal and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 09:31
L2	691	l1 and image adj1 sensor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 09:36

L3	1090	257/233,239.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 09:45
L4	1911	257/290-294.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 09:54
L5	1152	438/48,70.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:13
L7	3	(single adj1 crystal and image adj1 sensor).clm.	US-PGPUB	OR	OFF	2006/02/08 10:14
L8	51	(single adj1 crystal and sensor and electrode).clm.	US-PGPUB	OR	OFF	2006/02/08 10:15
L6	168	(single adj1 crystal and sensor). clm.	US-PGPUB	OR	OFF	2006/02/08 10:15